

VERSION SHOWING AMENDMENTS TO THE CLAIMS

This listing replaces all prior listings of the claims.

Claims:

Amend the claims as follows:

1 (Currently amended) A substrate and/or underlayer of an electronic component, which substrate or underlayer is to be coated with an organic functional layer, wherein said substrate or underlayer comprises a ~~partially crystalline and /or biaxially stretched~~ (well-ordered) plastic[[s]] film such the orderliness of the plastic[[s]] film enables the application of the functional material thereto in the form of a well-ordered layer to thereby increase the charge carrier mobility of the coated organic functional layer.

2 (Currently amended) A substrate as defined in claim 1, wherein the plastic[[s]] film is at least partially ~~crystalline and/or biaxially stretched~~.

Claim 3, canceled

4 (Currently amended). A substrate as defined in claims 1-3 ~~or 8~~, wherein the plastic[[s]] film is selected from any one of the group consisting of isotactic polypropylene, polyamide, polyethylene, or polyethylene terephthalate.

5 (Currently amended) A method of increasing the charge carrier mobility of a

conducting or semiconducting layer of organic material, wherein the conducting or semiconducting layer is formed on an underlayer-undersurface comprising an oriented, biaxially stretched (well-ordered) plastic[[s]] film.

6 (Currently amended) An OFET comprising an underlayer and a semiconducting layer on the underlayer according to The use of a substrate and/or underlayer as defined in any one of claims 1 to 3 and 8 for the production of an OFET.

7 (Currently amended). An organic field effect transistor (OFET) comprising a substrate or an underlayer which comprises a partially crystalline and/or biaxially stretched (well-ordered plastic[[s]] film) and above and on that substrate or underlayer a semiconducting layer of organic material, the semiconductor layer exhibiting a charge carrier mobility of $\mu > 10^{-3} \text{ cm}^2/\text{Vs}$

Claim 8, canceled.

9 (Currently amended) An OFET comprising an underlayer and a semiconducting layer on the underlayer according to The use of a substrate and/or underlayer as defined in claim 4 for the production of an OFET.